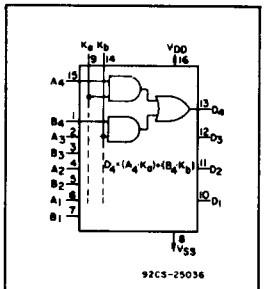
CD4019A Types

CMOS Quad AND/OR Select Gate

The RCA-CD4019A types are comprised of four AND/OR select gate configurations, each consisting of two 2-input AND gates driving a single 2-input OR gate. Selection is accomplished by control bits K_a and K_b. In addition to selection of either channel A or channel B information, the control bits can be applied simultaneously to accomplish the logical A + B function.

These types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic package (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix).



CD4019A
FUNCTIONAL DIAGRAM

MAXIMUM RATINGS, *Absolute-Maximum Values:*

STORAGE-TEMPERATURE RANGE (T_{stg}) . . . . . −65 to +150°C
OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPES D, F, K, H . . . . . −55 to +125°C
PACKAGE TYPE E . . . . . −40 to +85°C
DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal): . . . . . −0.5 to +15 V
POWER DISSIPATION PER PACKAGE (P_D)
FOR T_A = −40 to +60°C (PACKAGE TYPE E) . . . . . 500 mW
FOR T_A = +60 to +85°C (PACKAGE TYPE E) . . . . . Derate Linearly at 12 mW/°C to 200 mW
FOR T_A = −55 to +100°C (PACKAGE TYPES D, F, K) . . . . . 500 mW
FOR T_A = +100 to +125°C (PACKAGE TYPES D, F, K) . . . Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (ALL PACKAGE TYPES) . . . . . 100 mW
INPUT VOLTAGE RANGE, ALL INPUTS . . . . . −0.5 to V_{DD} +0.5 V
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ±0.79 mm) from case for 10 s max . . . . . +265°C

RECOMMENDED OPERATING CONDITIONS
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	V_{DD} (V)	LIMITS				UNITS
		D, F, K, H Packages		*E Package*		
		Min.	Max.	Min.	Max.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)		3	12	3	12	

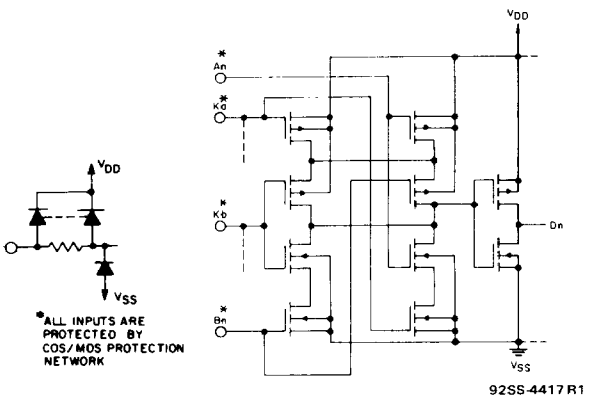


Fig. 1 – Schematic diagram for 1 of 4 identical stages.

Features:

- **Medium-speed operation . . . . . $t_{PHL} = t_{PLH}$ = 50 ns (typ.) at C_L = 15 pF, V_{DD} = 10 V**
- **Quiescent current specified to 15 V**
- **Maximum input leakage current of 1 μA at 15 V (full package-temperature range)**
- **1-V noise margin (full package-temperature range)**

Applications:

- **AND-OR select gating**
- **Shift-right/shift-left registers**
- **True/complement selection**
- **AND/OR/Exclusive-OR selection**

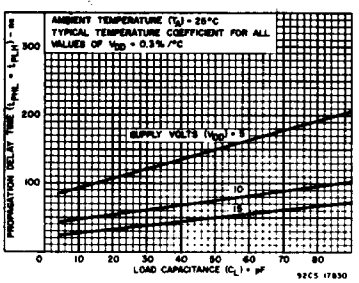


Fig. 2 – Typical propagation delay time vs. load capacitance.

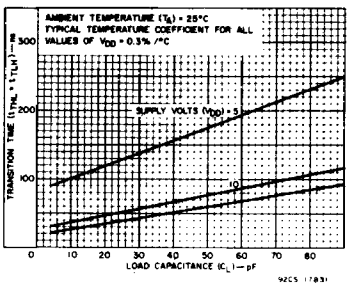


Fig. 3 – Typical transition time vs. load capacitance.

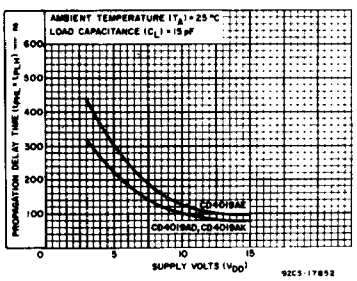


Fig. 4 – Maximum propagation delay time vs. supply voltage.

STATIC ELECTRICAL CHARACTERISTCS

Characteristic	Conditions			Limits at Indicated Temperatures (°C)								Units
				D, F, K, H Packages				E Package				
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	+25 Typ.	+25 Limit	+125	−40	+25 Typ.	+25 Limit	+85	
Quiescent Device Current, I_L Max.	–	–	5	5	0.03	5	300	50	0.1	50	700	μA
	–	–	10	10	0.05	10	600	100	0.2	100	1400	
	–	–	15	50	1	50	2000	500	5	500	5000	
Output Voltage: Low-Level, V_{OL}	–	5	5	0 Typ.; 0.05 Max.								V
	–	10	10	0 Typ.; 0.05 Max.								
High Level V_{OH}	–	0	5	4.95 Min.; 5 Typ.								
	–	0	10	9.95 Min.; 10 Typ.								
Noise Immunity: Inputs Low, V_{NL}	3.6	–	5	1.5 Min.; 2.25 Typ.								V
	7.2	–	10	3 Min.; 4.5 Typ.								
Inputs High V_{NH}	1.4	–	5	1.5 Min.; 2.25 Typ.								
	2.8	–	10	3 Min.; 4.5 Typ.								
Noise Margin: Inputs Low, V_{NML}	4.5	–	5	1 Min.								V
	9	–	10	1 Min.								
Inputs High, V_{NMH}	0.5	–	5	1 Min.								
	1	–	10	1 Min.								
Output Drive Current: n-Channel (Sink) I_{DN} Min.	0.5	–	5	0.6	0.9	0.45	0.3	0.37	1	0.3	0.23	mA
	0.5	–	10	0.9	1.5	0.75	0.55	0.8	1.5	0.65	0.5	
p-Channel (Source): I_{DP} Min.	4.5	–	5	-0.31	-0.5	-0.25	-0.175	-0.145	-0.5	-0.12	-0.095	
	9.5	–	10	-0.95	-1.5	-0.7	-0.5	-0.6	-1.5	-0.5	-0.4	
Input Leakage Current, I_{IL}, I_{IH}	Any Input	–	15	$\pm 10^{-5}$ Typ., ±1 Max.								μA

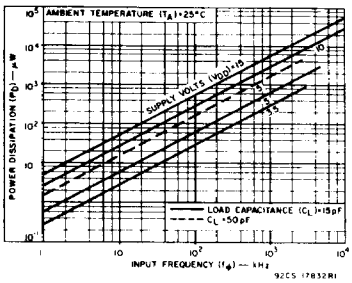


Fig. 5 — Typical dissipation characteristics. (per output).

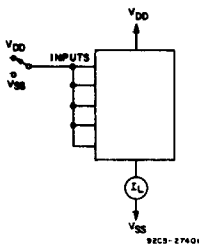


Fig. 6 — Quiescent-device-current test circuit.

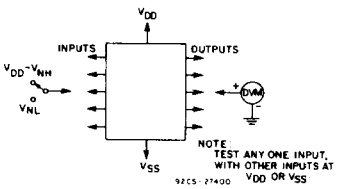


Fig. 7 — Noise-immunity test circuit.

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C, Input t_r, t_f = 20 ns, C_L = 15 pF, R_L = 200 kΩ

CHARACTERISTIC	TEST CONDITIONS		LIMITS						UNITS
			D, F, K, H Packages			E Package			
		V_{DD} (V)	Min.	Typ.	Max.	Min.	Typ.	Max.	
Propagation Delay Time; t_{PLH}, t_{PHL}		5	–	100	225	–	100	300	ns
		10	–	50	100	–	50	125	
Transition Time; t_{THL}, t_{TLH}		5	–	100	200	–	100	275	ns
		10	–	40	65	–	40	80	
Average Input Capacitance, C_I	All A and B Inputs		–	5	–	–	5	–	pF
	K_a and K_b Inputs		–	12	–	–	12	–	pF

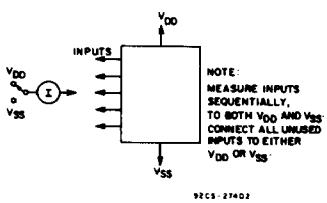


Fig. 8 — Input-leakage-current test circuit.